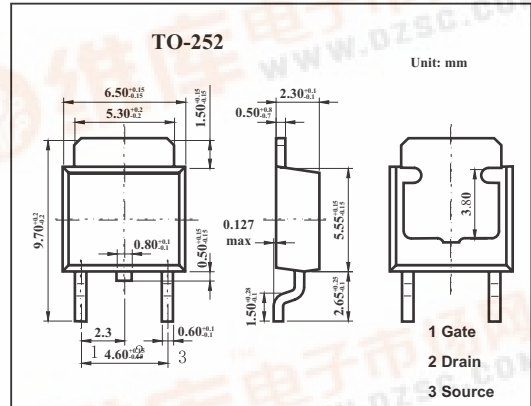


SMD Type MOSFET

MOS Field Effect Transistor
2SK3366

■ Features

- Super low on-state resistance:
 $R_{DS(on)1} = 21\text{ m}\Omega$ MAX. ($V_{GS} = 10\text{ V}$, $I_D = 10\text{ A}$)
 $R_{DS(on)2} = 33\text{ m}\Omega$ MAX. ($V_{GS} = 4.5\text{ V}$, $I_D = 10\text{ A}$)
 $R_{DS(on)3} = 43\text{ m}\Omega$ MAX. ($V_{GS} = 4\text{ V}$, $I_D = 10\text{ A}$)
- Low C_{iss} : $C_{iss} = 730\text{ pF}$ TYP.
- Built-in gate protection diode



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{bss}	30	V
Gate to source voltage	V_{gss}	± 20	V
Drain current	I_D	± 30	A
	I_{dp}^*	± 80	A
Power dissipation	P_D	$T_A=25^\circ\text{C}$	1.0
		$T_C=25^\circ\text{C}$	30
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 10\ \mu\text{s}$, Duty Cycle $\leq 1\%$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain cut-off current	I_{DSS}	$V_{DS}=30\text{V}, V_{GS}=0$			10	μA
Gate leakage current	I_{GSS}	$V_{GS}=\pm 20\text{V}, V_{DS}=0$			± 10	μA
Gat cutoff voltage	$V_{GS(off)}$	$V_{DS}=10\text{V}, I_D=1\text{mA}$	1.5	2.0	2.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=10\text{V}, I_D=10\text{A}$	5	10		S
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}, I_D=10\text{A}$		17.2	21	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_D=10\text{A}$		26	33	$\text{m}\Omega$
		$V_{GS}=4.0\text{V}, I_D=10\text{A}$		33	43	$\text{m}\Omega$
Input capacitance	C_{iss}	$V_{DS}=10\text{V}, V_{GS}=0, f=1\text{MHZ}$		730		pF
Output capacitance	C_{oss}			250		pF
Reverse transfer capacitance	C_{rss}			120		pF
Turn-on delay time	t_{on}			28		ns
Rise time	t_r	$I_D=10\text{A}, V_{GS(on)}=10\text{V}, R_G=10\ \Omega, V_{DD}=15\text{V}$		420		ns
Turn-off delay time	t_{off}			47		ns
Fall time	t_f			64		ns
Total Gate Charge	Q_G	$V_{DD} = 24\text{V}, V_{GS} = 10\text{V}, I_D = 20\text{A}$		15		nC
Gate to Source Charge	Q_{GS}			2.8		nC
Gate to Drain Charge	Q_{GD}			4.1		nC

